IMPROVING VERY HIGH TEMPERATURE THERMOELECTRIC PERFORMANCE OF Yb₄Sb₃ THROUGH DUAL SUBSTITUTIONS : A THEORETICAL STUDY

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Context

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120 -		Yb	Sb				- 8200	

Rare-earth antimonides with the anti-Th₃P₄ crystal structure were reported as potential candidates for high-temperature applications. Out of the four compositions reported in 2009 [1], the binary compound Yb₄Sb₃ stood out as the most promising composition : its Seebeck coefficient was the highest and reached 70 µV/K at 1300 K, and it was the only ptype thermoelectric conductor of the family.

Improvement attempts were conducted by substituting Yb atoms with another rare-earth, for instance with La or Sm, or by substituting Sb atoms with another pnictogen, such as Bi. Reported results show that lanthanum substitution improves thermoelectric properties, whereas bismuth substitution makes little to no change, as shown on the figure on the right.

In order to understand these differences in behaviour, the electronic structure of the La- and Bi-substituted compounds and their transport properties will be simulated.



Thermoelectricity?

A thermoelectric material directly transforms a temperature gradient into an electrical current (Seebeck effect), or transfers heat when an electrical current is applied (Peltier effect).

For a given material, the higher the thermoelectric figure of merit ZT, the better the thermoelectric performances

Electric conductivity

Seebeck coefficient

Computational details

- DOS calculated with VASP [2] code (v. 6.2.0) on optimized structures, PBE functional, 7x7x7 k-points
- Band-structure computed with VASP, PBE functional, 50 k-points per line
- Transport properties simulated with BoltzTraP2 [3] (v. 24.1.1) on a **VASP** DOS calculation with 11x11x11 k-points



Density of states



- Around the Fermi level in Yb_4Sb_3 : heavy band of f states belonging to Yb playing an important role in conduction
- In Yb₄Sb_{2.75}Bi_{0.25} : no big changes in the electronic structure. Sb states in the valence band are replaced by Bi states at the same place \rightarrow no real effect on transport properties
- In Yb_{3.75}La_{0.25}Sb₃: states of the heavy band shifted towards the conduction band \rightarrow will affect the transport properties

Effect of substitution on thermoelectric properties



• Around the Fermi level : better Seebeck coefficients to be achieved without tweaking too much the carrier concentration

• No noticeable difference between Yb₄Sb₃ and Yb₄Sb_{2.75}Bi_{0.25} as expected

• Interest in pushing the rare-earth substitution to achieve event better Seebeck coefficients

Conclusion

- Bi substitution has no effect neither on electronic properties nor on transport properties
- La substitution shifts some rare-earth states from the valence to the conduction band, which modifies the transport properties
- Better Seebeck coefficients seem to be easily reachable without tuning too much the carrier concentration
- Interest in substituting the compounds further but not too much, as the compound is not monophasic anymore after Yb_{3.5}La_{0.5}Sb₃

[1] Chamoire *et al.*, Dalton Trans. **2010**, *39*, 1118-1123 [2] Kresse et al., J. Phys. Rev. B. **1993**, 47, 558-561

[3] Madsen et al., J. Comput. Phys. Commun., 2018, 175, 67-71 [4] Bouteiller *et al.,* Mater. Adv., **2024**, *5*, 1217-1225